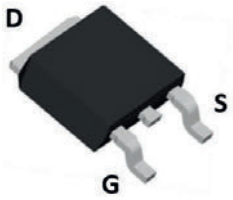
GOOD-ARK SEMICONDUCTOR

GSJD60R360

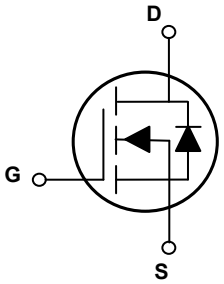
600V N-Channel MOSFET

Main Product Characteristics

$V_{(BR)DSS}$	600V
$R_{DS(ON)}$	0.36Ω (max.)
I_D	11A



TO-252 (DPAK)



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

RoHS Compliant

Description

The GSJD60R360 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_J=25°C unless otherwise specified)

Parameter	Symbol	Parameter.	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-to-Source Voltage	V_{GS}	±30	V
Continuous Drain Current, @ Steady-State (T_C=25°C)	I_D	11	A
Continuous Drain Current, @ Steady-State (T_C=100°C)		7	A
Pulsed Drain Current	I_{DM}	44	A
Power Dissipation (T_C=25°C)	P_D	89	W
		0.71	W/°C
Single Pulse Avalanche Energy[1]	E_{AS}	310	mJ
Single Pulse Avalanche Current	I_{AS}	2.6	A
Body Diode Reverse Voltage Slope[2]	dv/dt	50	V/ns
MOS dv/dt Ruggedness[3]	dv/dt	100	V/ns
Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	62	°C/W
Junction-to-Case	$R_{\theta JC}$	1.4	°C/W
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +150	°C
Soldering Temperature	T_{sold}	260	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	600	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	V_{DS}=600V, V_{GS}=0V, T_J=25°C	-	-	1.0	μA
		V_{DS}=600V, V_{GS}=0V, T_J=125°C	-	1.5	-	μA
Gate-to-Source Forward Leakage	I_{GSS}	V_{DS}=0V, V_{GS}=30V	-	-	100	nA
		V_{DS}=0V, V_{GS}=-30V	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5.5A	-	0.3	0.36	Ω
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2.5	-	4.0	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=100V, f=1MHz	-	925	-	pF
Output Capacitance	C_{oss}		-	35	-	
Reverse Transfer Capacitance	C_{rss}		-	1.0	-	
Total Gate Charge[4,5]	Q_g	I_D=11A, V_{DD}=480V, V_{GS}=10V	-	30	-	nC
Gate-to-Source Charge[4,5]	Q_{gs}		-	7.5	-	
Gate-to-Drain ("Miller") Charge[4,5]	Q_{gd}		-	15	-	
Gate Plateau[4,5]	$V_{plateau}$		-	6.7	-	V
Turn-on Delay Time[4,5]	$t_{d(on)}$	V_{DD}=300V, V_{GS}=10V, R_G=10Ω, I_D=11A	-	15	-	nS
Rise Time[4,5]	t_r		-	30	-	
Turn-Off Delay Time[4,5]	$t_{d(off)}$		-	45	-	
Fall Time[4,5]	t_f		-	25	-	
Gate Resistance	R_g	f=1MHz	-	3.7	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	T_C=25°C, MOSFET symbol showing the integral reverse p-n junction diode.	-	-	11	A
Diode Pulse Current	$I_{S,\ pulse}$		-	-	44	A
Diode Forward Voltage	V_{SD}	I_S=11A, V_{GS}=0V	-	-	1.4	V
Reverse Recovery Time[4]	T_{rr}	Is=11A, V_{GS}=0V, dI_F/dt=100A/us	-	306	-	nS
Reverse Recovery Charge[4]	Q_{rr}		-	3.7	-	μC
Reverse Recovery Peak Current[4]	I_{rrm}		-	24	-	A

Note:

1. L=79mH, V_{DD}=100V, R_G=25Ω, starting temperature T_J=25°C.
2. V_{DS}=0-400V, I_{SD}<=I_S, T_J=25°C.
3. V_{DS}=0-480V.
4. Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%.
5. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

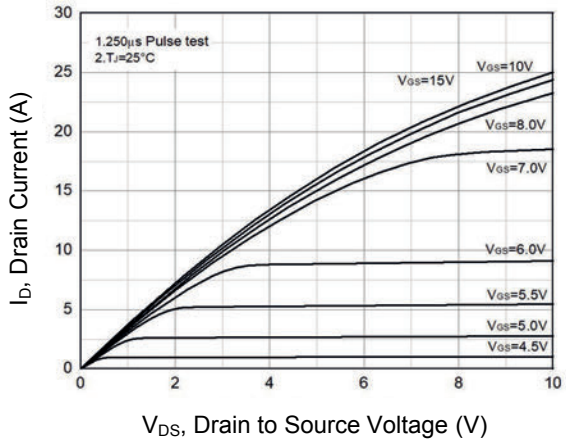


Figure 1. Typical Output Characteristics

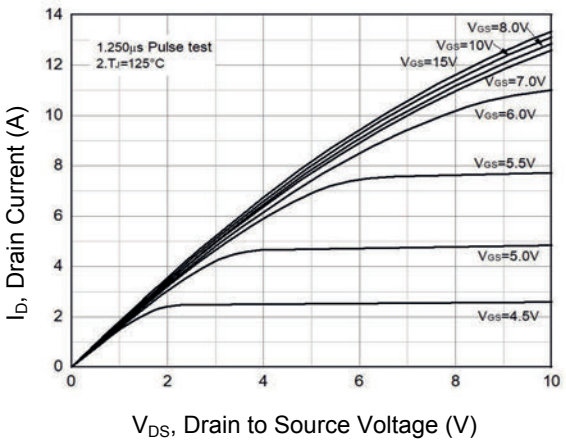


Figure 2. Typical Output Characteristics

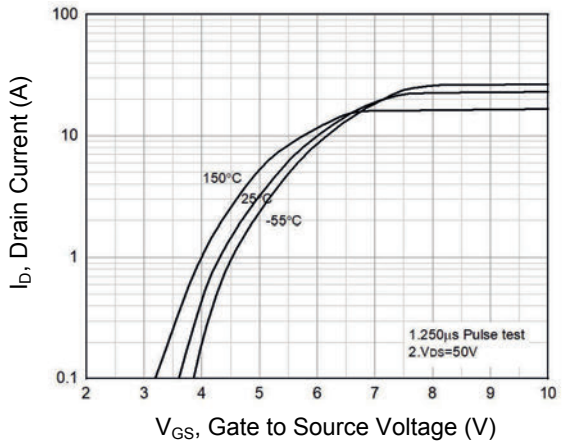


Figure 3. Transfer Characteristics

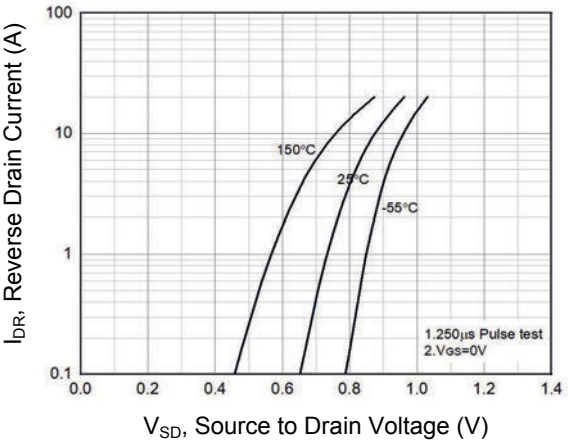


Figure 4. Body Diode Characteristics

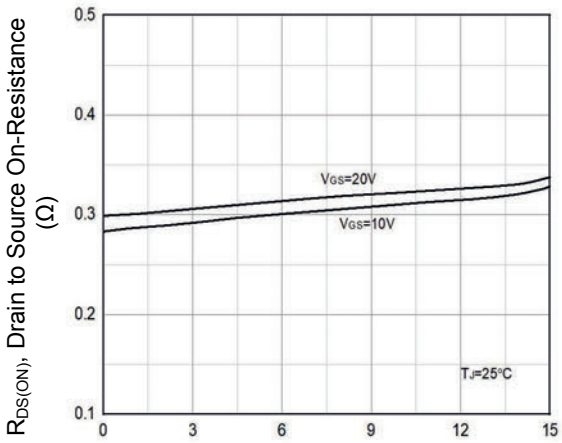


Figure 5. $R_{DS(ON)}$ Vs. Drain Current

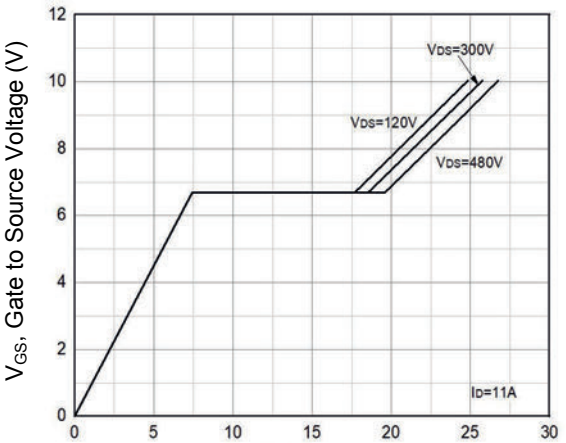


Figure 6. Gate Charge Characteristics

Typical Electrical and Thermal Characteristic Curves

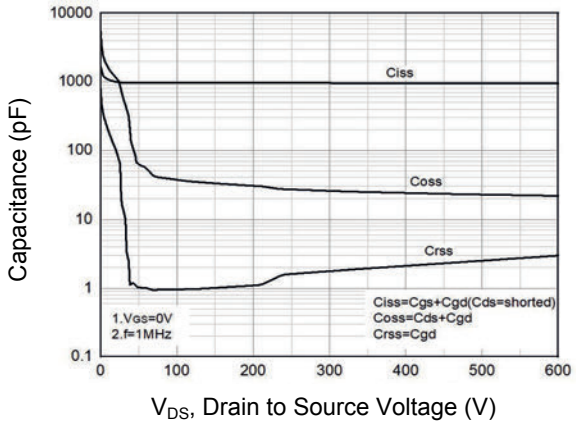


Figure 7. Capacitance Characteristics

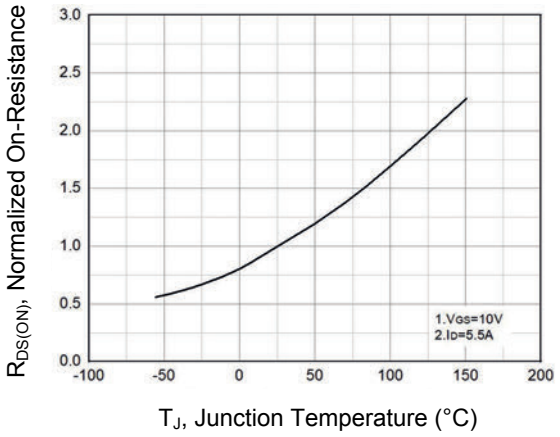


Figure 8. Normalized $R_{DS(ON)}$ Vs. T_J

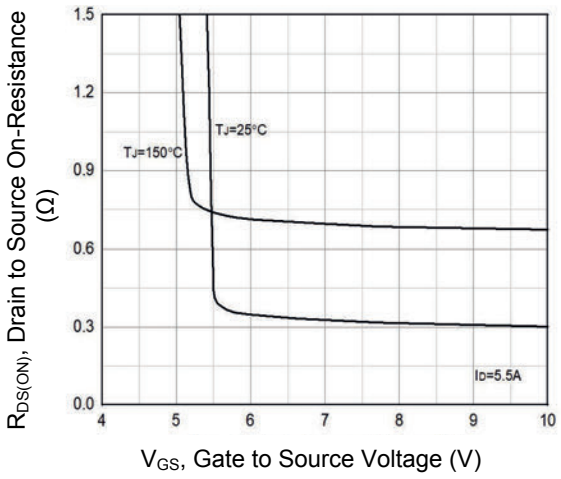


Figure 9. $R_{DS(ON)}$ Vs. V_{GS}

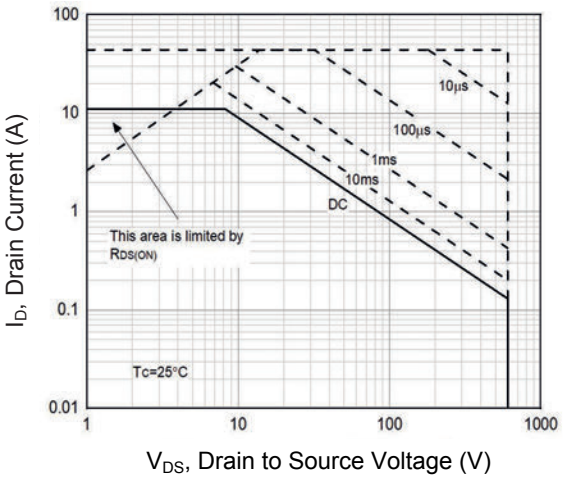


Figure 10. Safe Operation Area

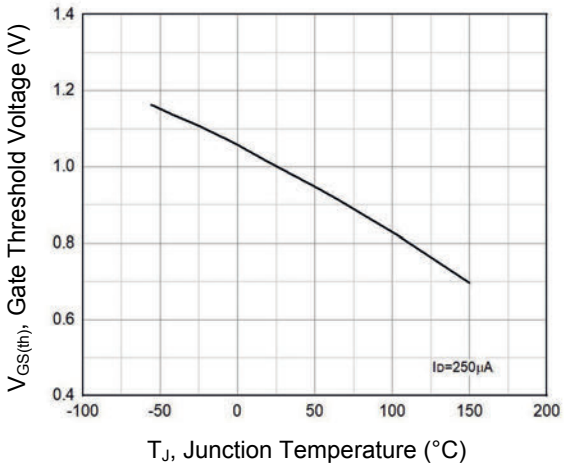


Figure 11. Gate Threshold Voltage Vs. T_J

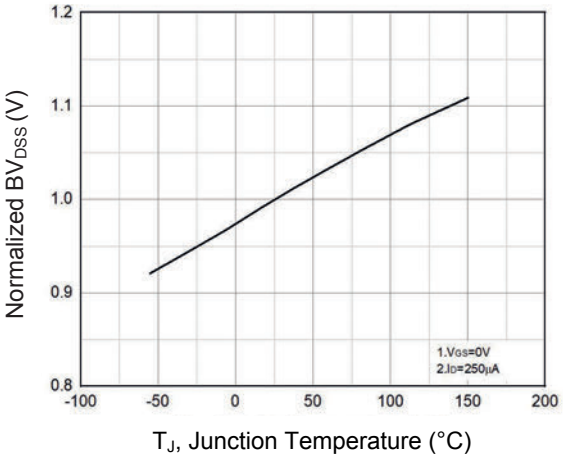


Figure 12. Normalized BV_{DSS} Vs. T_J

Typical Electrical and Thermal Characteristic Curves

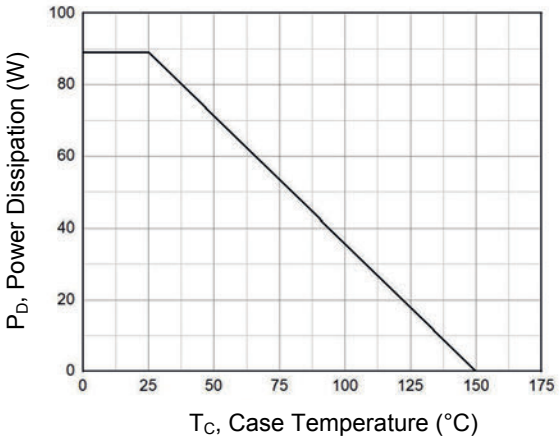


Figure 13. Power Dissipation Vs. T_C

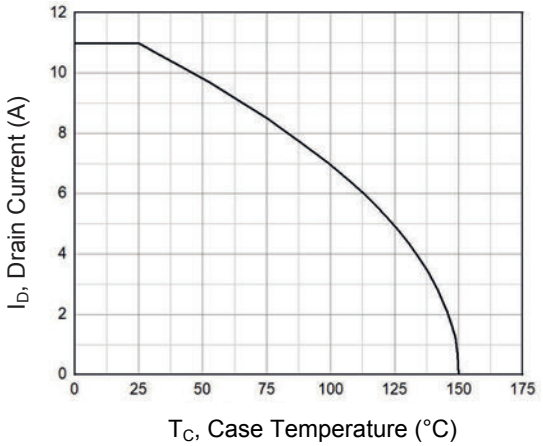


Figure 14. Drain Current Vs. T_C

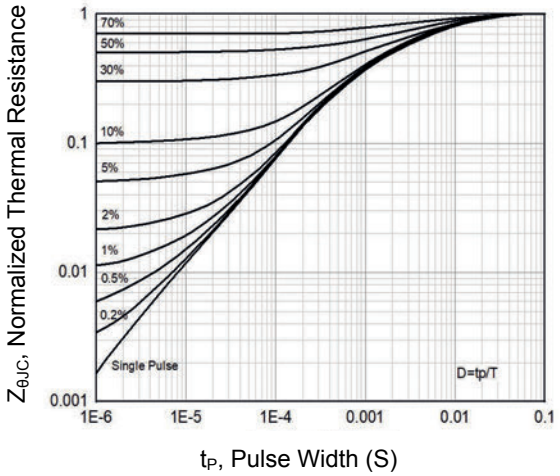
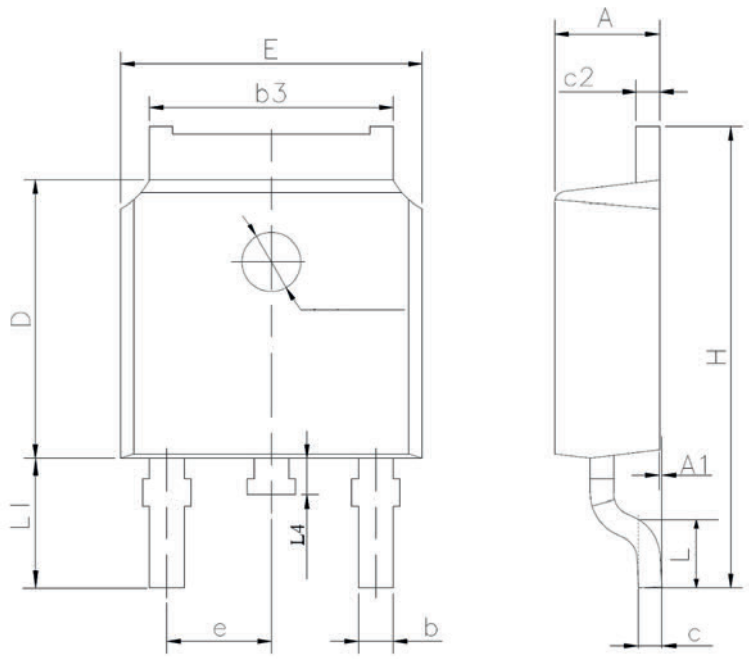


Figure 15. Transient Thermal Impedance Vs. t_P

Package Outline Dimensions TO-252(DPAK)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.100	2.500	0.083	0.098
A1	0.000	0.127	0.000	0.005
b	0.660	0.890	0.026	0.035
b3	5.100	5.460	0.201	0.215
c	0.450	0.650	0.018	0.026
c2	0.450	0.650	0.018	0.026
D	5.800	6.400	0.228	0.252
E	6.300	6.900	0.248	0.272
e	2.300 TYP		0.091 TYP	
H	9.600	10.600	0.378	0.417
L	1.400	1.700	0.055	0.067
L1	2.900 REF		0.114 REF	
L4	0.600	1.000	0.024	0.039